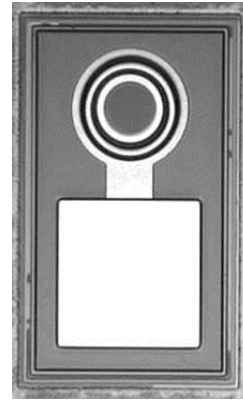




Features

- : 650 nm wavelength range
- : low current bias
- : Other configurations available on request

Description



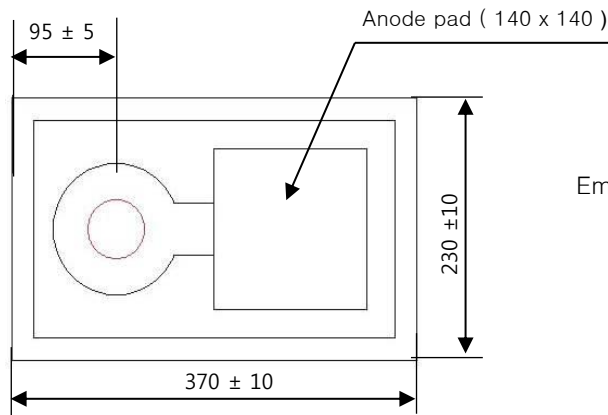
Applications

- : Industrial applications
- : Sensors

Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	-40 to 100 °C
Operating Temperature	-20 to 70 °C
Continuous Forward Current	10mA
Continuous Reverse Voltage	5V (@10µA)

Dimensions



Emission area : Ø 50 µm

Unit : µm

Die Height : 200 ± 15 µm



Electro-Optics Characteristics ($T_a=25^\circ\text{C}$ unless otherwise stated)

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Total Radiant Flux	Φ_o	0.2			mW	$I_f = 5\text{mA}$
Peak Wavelength	λ_p	640	650	665	nm	$I_f = 5\text{mA}$
Forward Voltage	V_f		2.1	2.25	V	$I_f = 5\text{mA}$
Breakdown Voltage	V_b		-10		V	

Test Data were measured in TO header of wire bonded chip

Value is referenced to the vender's measurement system (correlation to customer product is required).

Notes

* These specifications are subject to change without notice.



NOTICE

The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product